

MOSFET – Power, N-Channel, Dual, EFCP

24 V, 13 A, 11.5 mΩ

EFC6601R

Features

- 2.5 V Drive
- Common-drain Type
- 2 kV ESD HBM
- Protection Diode In
- This Device is Pb–Free, Halogen Free/BFR Free and is RoHS Compliant

Specifications

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	V _{SSS}		24	٧
Gate-to-Source Voltage	V _{GSS}	V _{GSS}		٧
Source Current (DC)	Is		13	Α
Source Current (Pulse)	I _{SP}	PW ≤ 10 μs, duty cycle ≤1%	60	Α
Total Dissipation	P _T	When mounted on ceramic substrate (5000 mm ² x 0.8 mm)	2.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		– 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



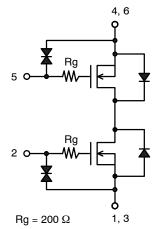
WLCSP6 1.81x2.70 / EFCP2718-6CE-020 CASE 567HS

MARKING DIAGRAM

MA YMZZ

MA = Specific Device Code
Y = Year of Production
M = Assembly Operation Month
ZZ = Assembly Lot Number

ELECTRICAL CONNECTION



PIN ASSIGNMENT

6 5 4

2

- 1: Source1 2: Gate1
- 3: Source1
- 4: Source2
- 5: Gate2
- 6: Source2

ORDERING INFORMATION

Device	Package	Shipping
EFC6601R-TR	EFCP (Pb-Free and Halogen Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$

Parameter	Symbol	Conditions		Min	Тур	Max	Unit
Source-to-Source Breakdown Voltage	V _{(BR)SSS}	I _S = 1 mA, V _{GS} = 0 V	Test Circuit 1	24	-	-	V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} = 20 V, V _{GS} = 0 V	Test Circuit 1	-	-	1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$	Test Circuit 2	-	-	±1	μΑ
Cutoff Voltage	V _{GS} (off)	V _{SS} = 10 V, I _S = 1 mA	Test Circuit 3	0.5	-	1.3	V
Forward Transfer Admittance	yfs	V _{SS} = 10 V, I _S = 3 A	Test Circuit 4	-	15.5	-	S
Static Source-to-Source On-State	R _{SS} (on)1	I _S = 3 A, V _{GS} = 4.5 V	Test Circuit 5	6.6	9.5	11.5	mΩ
Resistance	R _{SS} (on)2	I _S = 3 A, V _{GS} = 4.0 V	Test Circuit 5	7.0	10	12	mΩ
	R _{SS} (on)3	I _S = 3 A, V _{GS} = 3.8 V	Test Circuit 5	7.3	10.5	13	mΩ
	R _{SS} (on)4	I _S = 3 A, V _{GS} = 3.1 V	Test Circuit 5	8.0	11.5	15	mΩ
	R _{SS} (on)5	I _S = 3 A, V _{GS} = 2.5 V	Test Circuit 5	9.0	13	17	mΩ
Turn-ON Delay Time	t _d (on)	$V_{DD} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$	Test Circuit 7	-	280	-	ns
Rise Time	t _r	I _S = 3 A		-	630	-	ns
Turn-OFF Delay Time	t _d (off)			-	53000	-	ns
Fall Time	t _f			-	47000	-	ns
Total Gate Charge	Qg	V _{DD} = 10 V, V _{GS} = 4.5 V, I _S = 13 A	Test Circuit 8	-	48	-	nC
Forward Source-to-Source Voltage	V _{F(S-S)}	I _S = 3 A, V _{GS} = 0 V	Test Circuit 6	-	0.76	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Test circuits are example of measuring FET1 side.

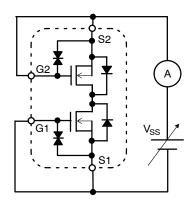
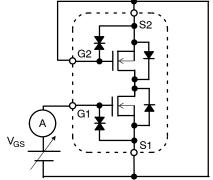


Figure 1. Test Circuit 1 – I_{SSS}



When FET1 is measured, Gate and Source of FET2 are short-circuited.

Figure 2. Test Circuit 2 - I_{GSS}

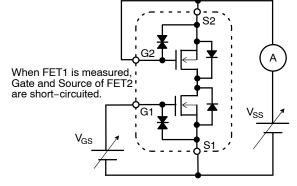


Figure 3. Test Circuit 3 - V_{GS}(off)

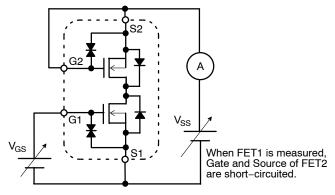


Figure 4. Test Circuit 4 - I yfs I

TEST CIRCUITS (continued)

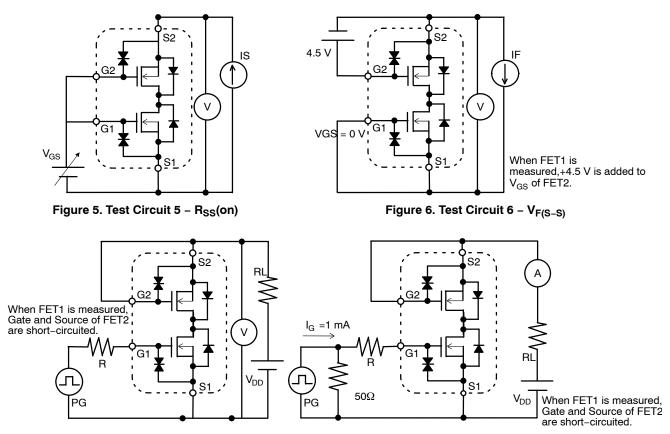


Figure 7. Test Circuit 7 – $t_d(on)$, t_r , $t_d(off)$, t_f

Figure 8. Test Circuit 8 - Qg

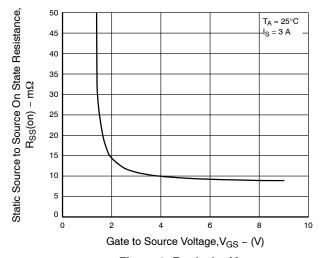


Figure 9. R_{SS} (on) – V_{GS}

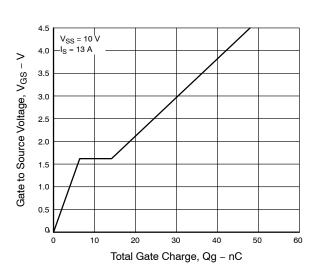


Figure 11. Qg - V_{GS}

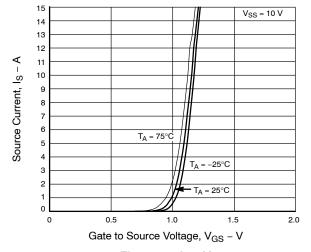


Figure 13. I_S - V_{GS}

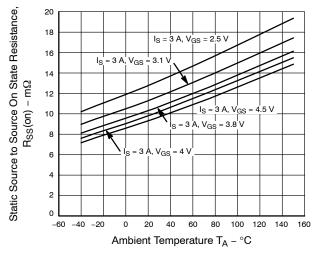


Figure 10. $R_{SS}(on) - T_A$

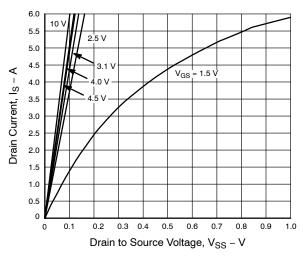


Figure 12. I_S - V_{SS}

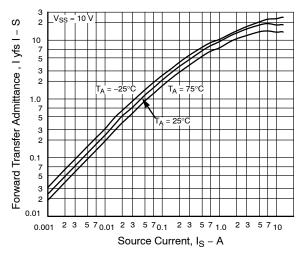


Figure 14. I yfs I - I_S

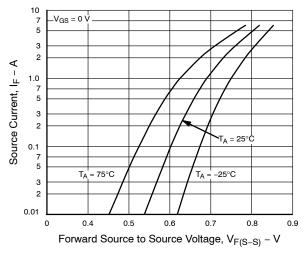


Figure 15. I_S - V_{F(S-S)}

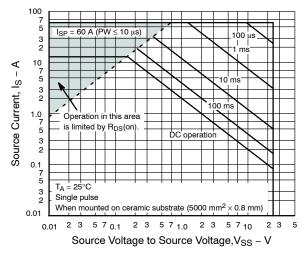


Figure 17. ASO

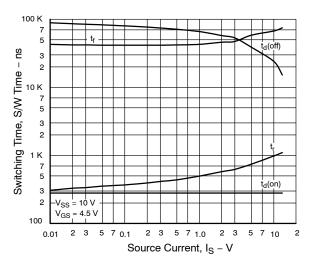


Figure 16. S/W Time - I_D

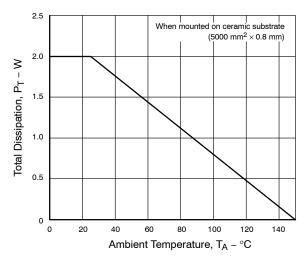
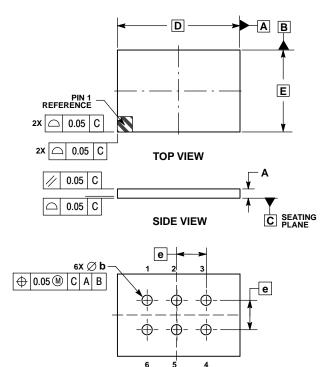


Figure 18. P_T – T_A



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DATE 14 NOV 2014

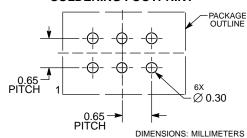


BOTTOM VIEW

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS						
DIM	MIN MAX						
Α	0.18	0.22					
b	0.27	0.33					
D	2.70 BSC						
E	1.81 BSC						
_	0.65 BSC						

RECOMMENDED SOLDERING FOOTPRINT*

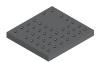


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PIN A1

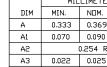
0.08 C

 \triangle 0.03 C

REFERENCE

WLCSP40 2.301x2.499x0.369 CASE 567HU **ISSUE 0**

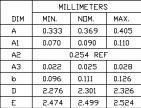
DATE 29 APR 2022

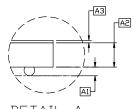


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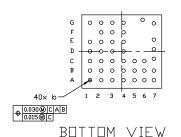
SEATING

C





DETAIL A SCALE 1:3

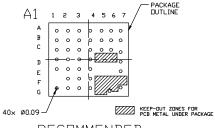


TOP VIEW

0.0.0.0.0.0

SIDE VIEW

DETAIL A-



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

NUTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 IS MEASURED AT THE MAXIMUM SOLDER BALL DIAMETER
- PARALLEL TO DATUM C.
 COPLANARITY APPLIES TO THE
 SPHERICAL CROWNS OF THE SOLDER
- BALLS.
 DATUM C, THE SEATING PLANE, IS
 DEFINED BY THE SPHERICAL CROWNS OF
 THE SOLDER BALLS.

BALL POSITION TABLE							
BALL	X	Υ		BALL	X	Υ	
A1	-1.00	-0.90		D1	-1.00	0.00	
A2	-0.65	-0.90		D2	-0.65	0.00	
A3	-0.30	-0.90		D3	-0.30	0.00	
Α4	0.05	-0.90		D4	0.05	0.00	
A5	0.40	-0.90		D7	1.00	0.07	
A6	0.70	-0.90		E1	-1.00	0.30	
A7	1.00	-0.90		E2	-0.65	0.30	
B1	-1.00	-0.60		E3	-0.30	0.30	
B2	-0.65	-0.60		E4	0.05	0.30	
В3	-0.30	-0.60		E7	1.00	0.37	
B4	0.05	-0.60		F2	-0.65	0.60	
B5	0.40	-0.60		F3	-0.30	0.60	
В6	0.70	-0.60		F4	0.05	0.60	
В7	1.00	-0.60		G1	-1.00	0.90	
C1	-1.00	-0.30		G2	-0.65	0.90	
C2	-0.65	-0.30		G3	-0.30	0.90	
С3	-0.30	-0.30		G4	0.05	0.90	
C4	0.05	-0.30		G6	0.65	0.99	
C5	0.40	-0.30		G7	1.00	0.88	
C6	0.70	-0.30					
C7	1.00	-0.23					

MOUNTING PAD POSITION TABLE							
BALL	X	Υ		BALL	X	Υ	
A1	-1.00	0.90		D1	-1.00	0.00	
A2	-0.65	0.90		D2	-0.65	0.00	
A3	-0.30	0.90		D3	-0.30	0.00	
Α4	0.05	0.90		D4	0.05	0.00	
A5	0.40	0.90		D7	1.00	-0.07	
A6	0.70	0.90		E1	-1.00	-0.30	
Α7	1.00	0.90		E2	-0.65	-0.30	
B1	-1.00	0.60		E3	-0.30	-0.30	
B2	-0.65	0.60		E4	0.05	-0.30	
ВЗ	-0.30	0.60		E7	1.00	-0.37	
B4	0.05	0.60		F2	-0.65	-0.60	
B5	0.40	0.60		F3	-0.30	-0.60	
В6	0.70	0.60		F4	0.05	-0.60	
В7	1.00	0.60		G1	-1.00	-0.90	
C1	-1.00	0.30		G2	-0.65	-0.90	
C2	-0.65	0.30		G3	-0.30	-0.90	
C3	-0.30	0.30		G4	0.05	-0.90	
C4	0.05	0.30		G6	0.65	-0.99	
C5	0.40	0.30		G7	1.00	-0.88	
C6	0.70	0.30					
C7	1.00	0.23					

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